

GSM3025S

30V N-Channel Enhancement Mode MOSFET

Product Description

GSM3025S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

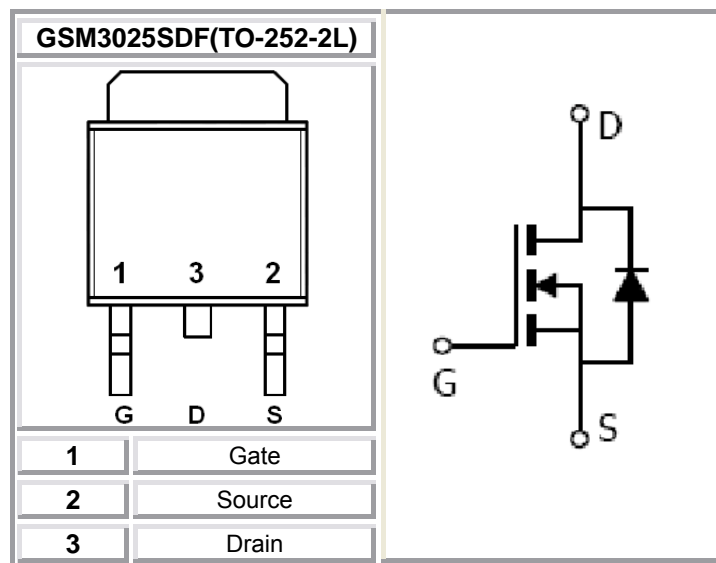
Features

- 30V/9.0A, $R_{DS(ON)}=32m\Omega@V_{GS}=10V$
- 30V/7.0A, $R_{DS(ON)}=36m\Omega@V_{GS}=4.5V$
- 30V/5.0A, $R_{DS(ON)}=42m\Omega@V_{GS}=2.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- TO-252-2L package design

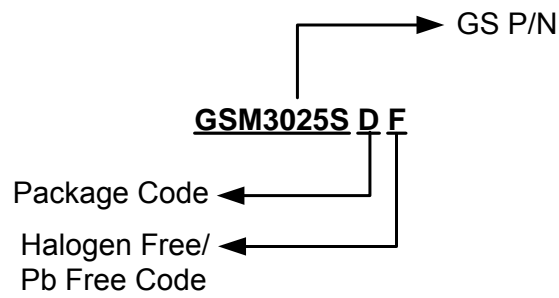
Applications

- DC/DC Converter
- Load Switch
- CCFL Inverter
- Power Management in Notebook Computer

Packages & Pin Assignments

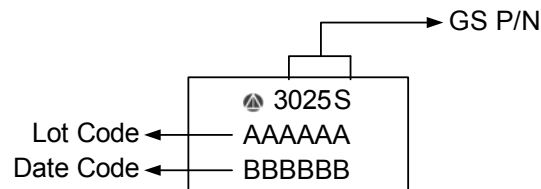


Ordering Information



Part Number	Package	Quantity Reel
GSM3025SDF	TO-252-2L	2500 PCS

Marking Information



Absolute Maximum Ratings

(T_A=25°C unless otherwise noted)

Symbol	Parameter	Typical	Unit
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate -Source Voltage	±12	V
I _D	Continuous Drain Current(T _J =150°C)	T _A =25°C	22
		T _A =70°C	16
I _{DM}	Pulsed Drain Current	45	A
I _S	Continuous Source Current(Diode Conduction)	9.0	A
P _D	Power Dissipation	T _A =25°C	40
		T _A =70°C	15
T _J	Operating Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55/150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient	62.5	°C/ W

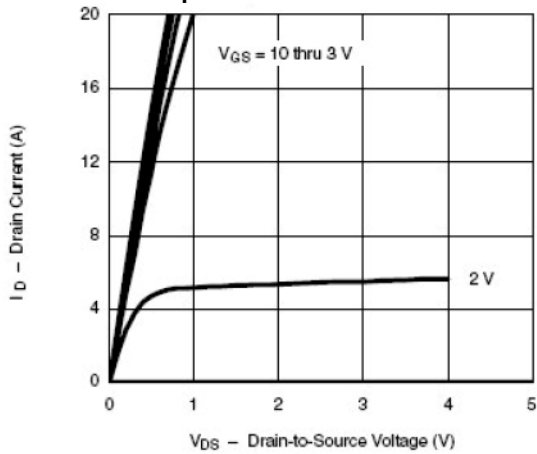
Electrical Characteristics

($T_A=25^\circ\text{C}$ unless otherwise noted)

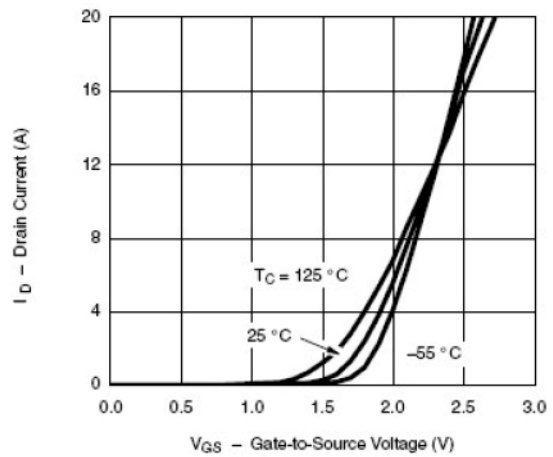
Symbol	Parameter	Conditions	Min.	Typ	Max.	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6		1.1	
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 16V$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24V, V_{GS}=0V$			1	uA
		$V_{DS}=24V, V_{GS}=0V, T_J=85^\circ\text{C}$			30	
$I_{D(on)}$	On-State Drain Current	$V_{DS}\geq 5V, V_{GS}=4.5V$	15			A
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=9.0A$		24	32	m Ω
		$V_{GS}=4.5V, I_D=7.0A$		26	36	
		$V_{GS}=2.5V, I_D=5.0A$		32	42	
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=6.1A$		20		S
V_{SD}	Diode Forward Voltage	$I_S=1.7A, V_{GS}=0V$		0.8	1.2	V
Dynamic						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$		320		pF
C_{oss}	Output Capacitance			70		
C_{rss}	Reverse Transfer Capacitance			30		
Q_g	Total Gate Charge	$V_{DS}=15V, V_{GS}=10V, I_D\cong 2.6A$		3.0	4.5	nC
Q_{gs}	Gate-Source Charge			1.6		
Q_{gd}	Gate-Drain Charge			0.6		
$t_{d(on)}$	Turn-On Time	$V_{DD}=15V, R_L=15\Omega, I_D\cong 1.0A, V_{GEN}=10V, R_G=6\Omega$		8	12	ns
t_r				12	18	
$t_{d(off)}$	Turn-Off Time			15	30	
t_f				8	15	

Typical Performance Characteristics

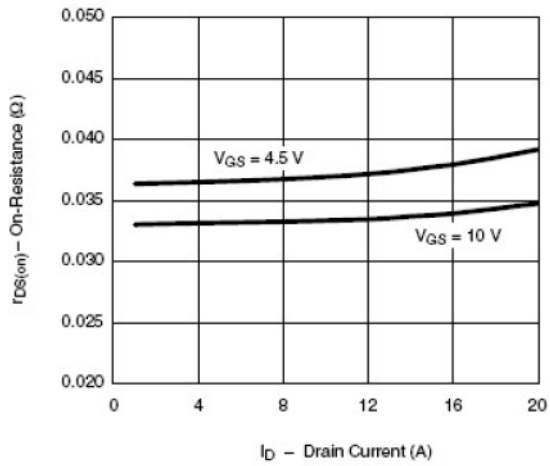
Output Characteristics



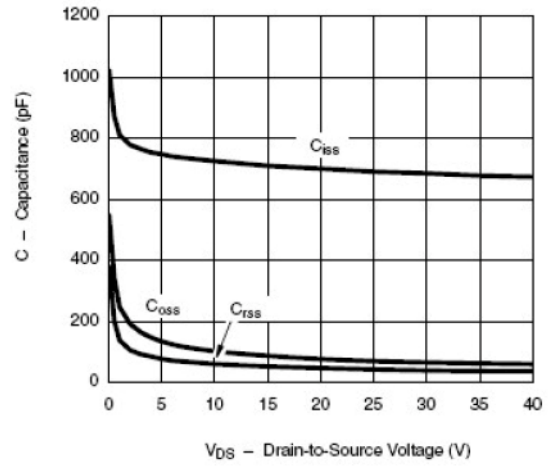
Transfer Characteristics



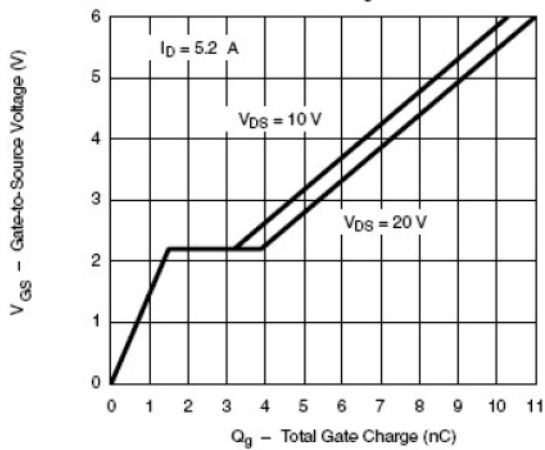
On-Resistance vs. Drain Current



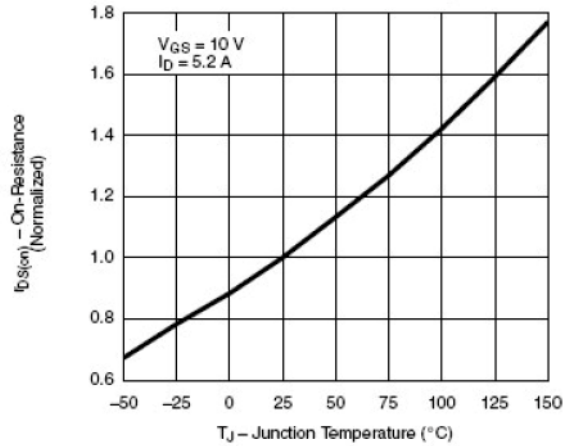
Capacitance



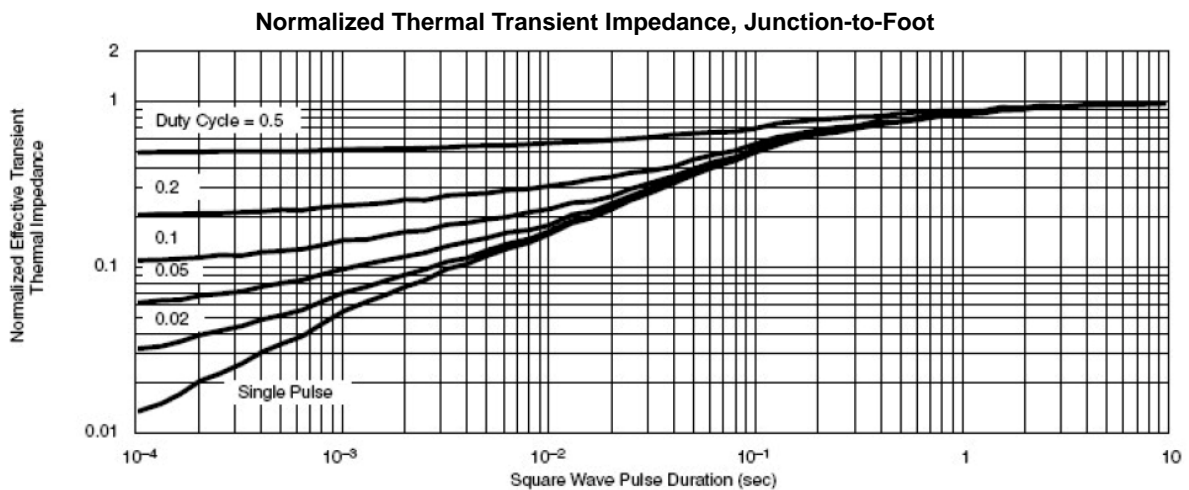
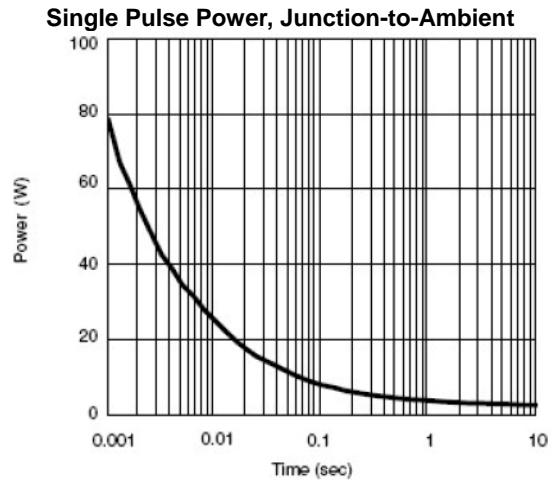
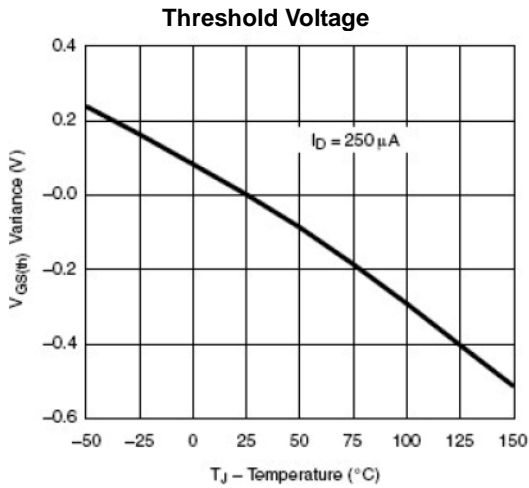
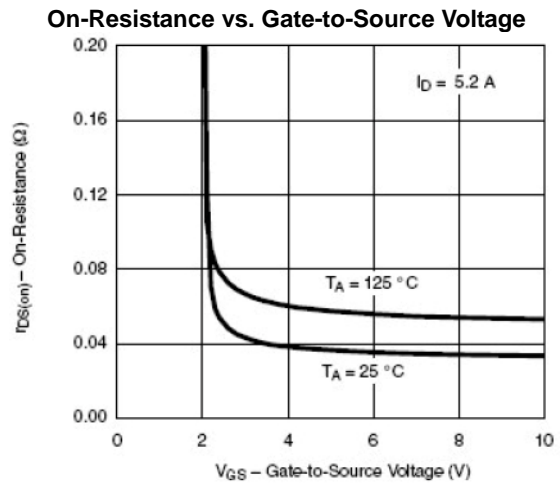
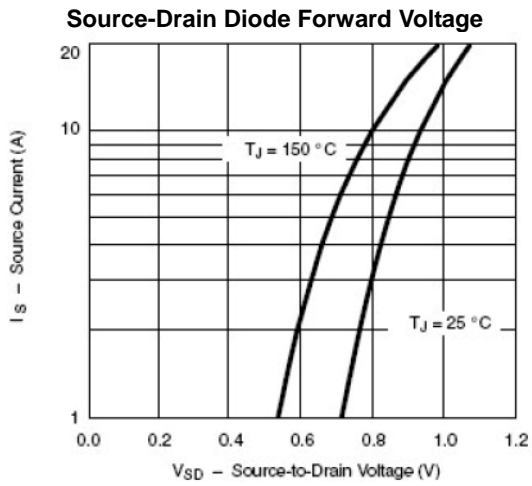
Gate Charge



On-Resistance vs. Junction Temperature

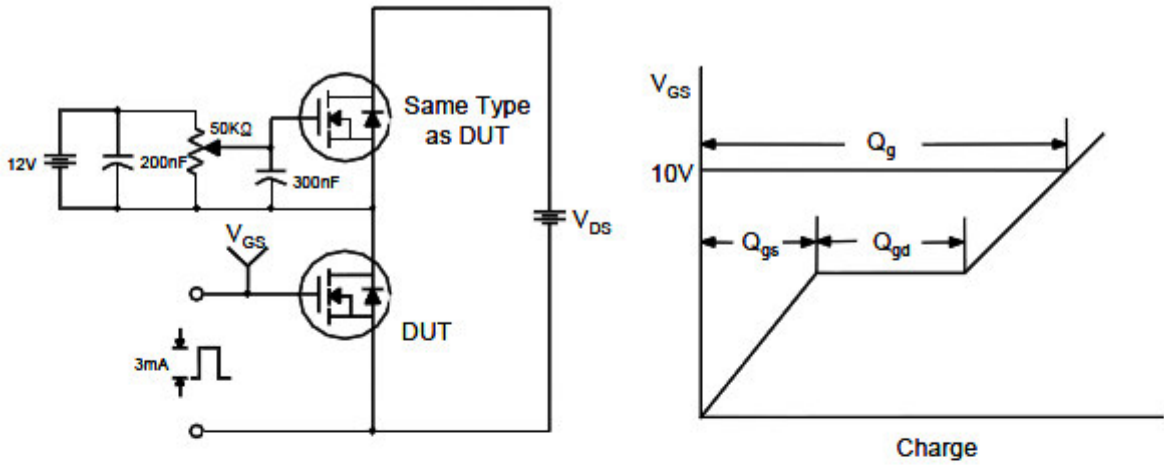


Typical Performance Characteristics (continue)

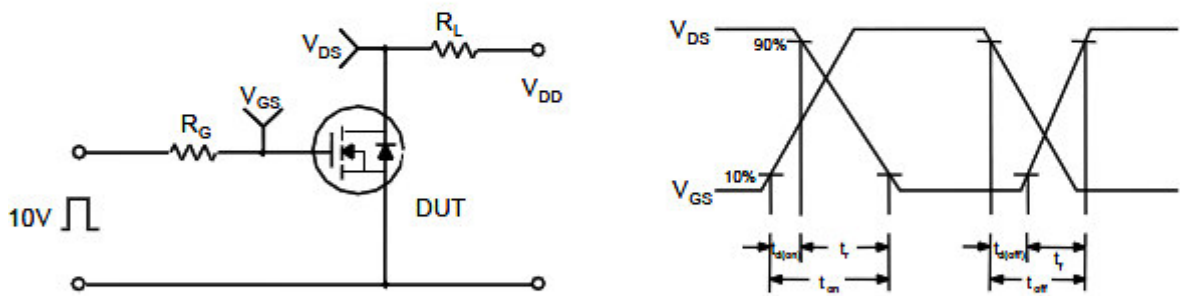


Typical Characteristics

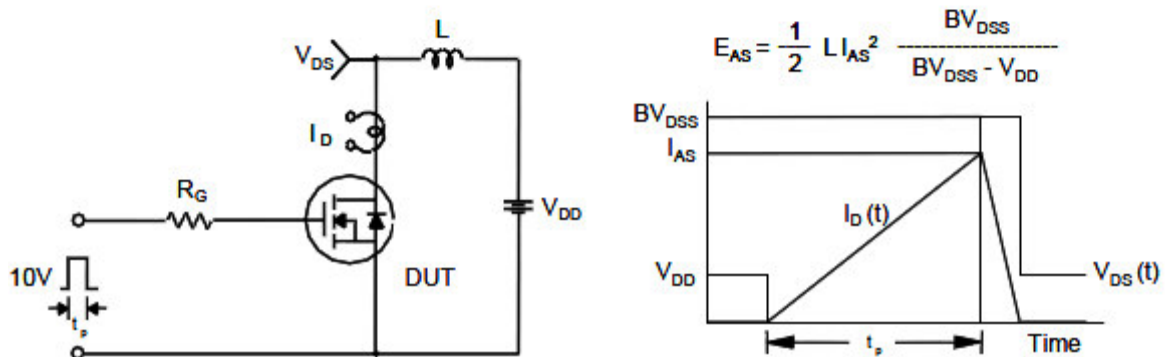
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

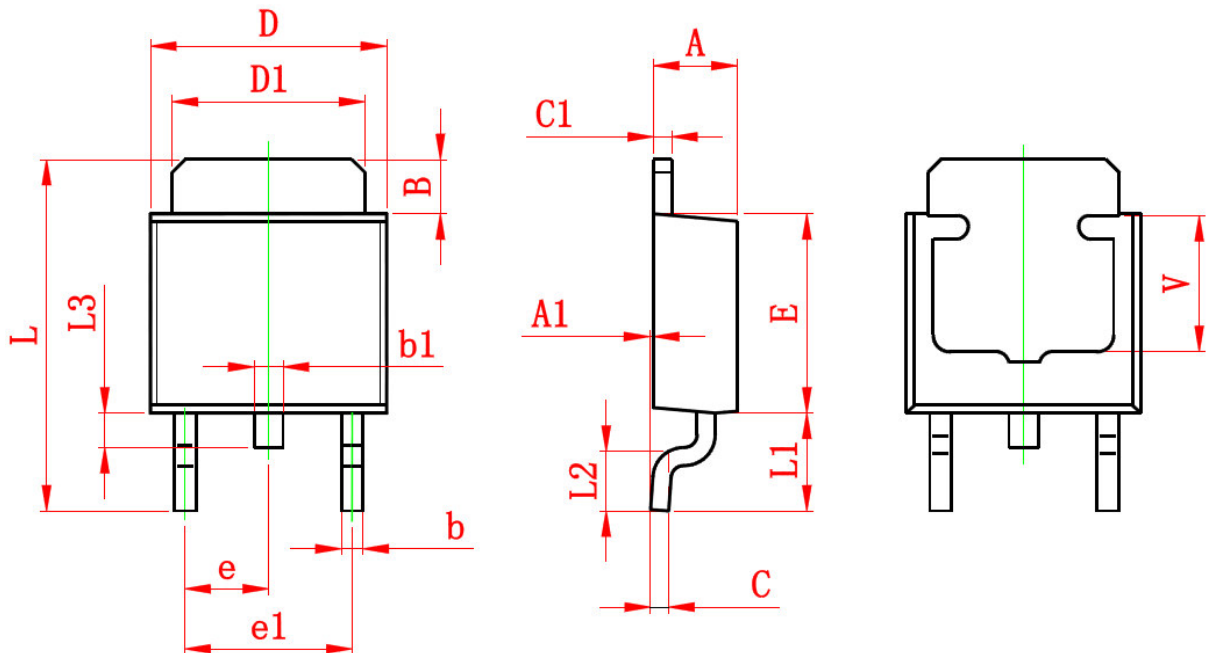


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

TO-252-2L PLASTIC PACKAGE











Dimensions				
SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP		0.091 TYP	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF		0.150 REF	



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